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2SC1470

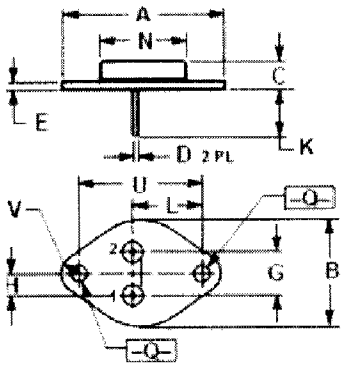
SILICON NPN POWER TRANSISTOR

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEV}	Collector-Emitter Voltage	850	V
$V_{CEO(SUS)}$	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	20	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current-Continuous	10	A
I_{BM}	Base Current-Peak	20	A
P_C	Collector Power Dissipation@T_C=25℃	250	W
T_J	Junction Temperature	200	℃
T_{stg}	Storage Temperature	-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	0.7	℃/W



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	**9.30**	**11.10**
D	0.90	1.10
E	**2.90**	**3.10**
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C=100mA ; I_B=0	450			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 10A; I_B= 1A			2.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 15A; I_B= 1.5A I_C= 15A; I_B= 1.5A,T_C=100℃			3.0 3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 15A; I_B= 1.5A I_C= 15A; I_B= 1.5A,T_C=100℃			1.5 1.5	V
I_{CEV}	Collector Cutoff Current	V_{CEV}=850V;$V_{BE(off)}$=1.5V V_{CEV}=850V;$V_{BE(off)}$=1.5V;T_C=100℃			0.25 1.5	mA
I_{CER}	Collector Cutoff Current	V_{CE}= 850V; R_{BE}= 50 Ω ,T_C= 100℃			2.5	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V; I_C=0			1.0	mA
h_{FE}	DC Current Gain	I_C= 20A ; V_{CE}= 5V	7			
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f_{test}=1.0kHz			500	pF

Switching times;Resistive Load

t_d	Delay Time	I_C= 15A , V_{CC}= 250V, R_{B2}= 1.6 Ω I_{B1}= 1.5A;I_{B2}= -3A, PW= 30 μ s Duty Cycle≤2.0%		20	50	ns
t_r	Rise Time			200	500	ns
t_s	Storage Time			900	2200	ns
t_f	Fall Time			100	250	ns